

CMOS LDO Regulator Series for Portable Equipments

Standard CMOS LDO Regulators



BH ____ FB1WG series, BH ____ FB1WHFV series, BH LB1WG series, BH LB1WHFV series

Large Current 300mA **CMOS LDO Regulators**

BH C MA3WHFV Series

No.09020EBT02

Description

The BH FB1W, BH LB1W and BH MA3W series are low dropout CMOS regulators with 150 mA and 300 mA output that have $\pm 1\%$ high accuracy output voltage.

The BH FB1W series combines 40µA low current consumption and a 70 dB high ripple rejection ratio by utilizing output level CMOS technology. The components can be easily mounted into the small standard SSOP5 and the ultra-small HVSOF5/HVSOF6 packages.

Features

1) High accuracy output voltage: ±1%

2) High ripple rejection ratio: 70 dB (BH FB1WHFV/WG, BH LB1WHFV/WG)

3) Low dropout voltage: 60 mV (when current is 100 mA) (BH MA3WHFV)

4) Stable with ceramic output capacitors

5) Low Bias current : 40µA (Io = 50 mA) (BH FB1WHFV/WG)

6) Output voltage ON/OFF control

7) Built-in over-current protection and thermal shutdown circuits

8) Ultra-small power package: HVSOF5 (BH FB1WHFV, BH LB1WHFV)

9) Ultra-small power package: HVSOF6 (BH MA3WHFV)

Applications

Battery-driven portable devices and etc.

Line up

■ 150mA BH FB1W and BH LB1W Series

| Part Number | 1.5 | 1.8 | 1.85 | 2.5 | 2.8 | 2.9 | 3.0 | 3.1 | 3.3 | Package |
|-------------|-----|-----|------|-----|-----|-----|-----|-----|-----|---------|
| BH FB1WG | - | - | - | ~ | V | V | V | V | ~ | SSOP5 |
| BH FB1WHFV | - | - | - | V | ~ | ~ | V | ~ | ~ | HVSOF5 |
| BHLB1WG | ~ | ~ | - | - | - | - | - | - | - | SSOP5 |
| BH LB1WHFV | ~ | V | ~ | _ | - | - | - | _ | _ | HVSOF5 |

300mA BH MA3WHFV series

| Part Number | 1.5 | 1.8 | 2.5 | 2.8 | 2.9 | 3.0 | 3.1 | 3.3 | Package |
|-------------|-----|-----|--------------|-----|-----|-----|-----|-----|---------|
| BH MA3WHFV | ~ | 7 | \checkmark | ~ | ~ | ~ | ~ | ~ | HVSOF6 |

Part Number: $\underline{B} \underline{H} \square F \underline{B} \underline{1} \underline{W} \square$, $\underline{B} \underline{H} \square \underline{L} \underline{B} \underline{1} \underline{W} \square$

Part Number: B H 🗌 M A 3 W 🗌 а

| | a | | o a | D | | | | | |
|--------|----------------------------|--------------------|-----------|--------------------|--|--|--|--|--|
| Symbol | Details | | | | | | | | |
| | Output Voltage Designation | | | | | | | | |
| | | Output Voltage (V) | | Output Voltage (V) | | | | | |
| | 15 | 1.5V (Typ.) | 29 | 2.9V (Typ.) | | | | | |
| а | 18 | 1.8V (Typ.) | 30 | 3.0V (Typ.) | | | | | |
| | 1J | 1.85V (Typ.) | 31 | 3.1V (Typ.) | | | | | |
| | 25 | 2.5V (Typ.) | 33 | 3.3V (Typ.) | | | | | |
| | 28 | 2.8V (Typ.) | | | | | | | |
| b | Package: | G : SSOP5 | HFV : HVS | OF5 | | | | | |

| Symbol | Details | | | | | | | | | |
|--------|----------------------------|--------------------|-----|--------------------|--|--|--|--|--|--|
| | Output Voltage Designation | | | | | | | | | |
| | | Output Voltage (V) | | Output Voltage (V) | | | | | | |
| | 15 | 1.5V (Typ.) | 29 | 2.9V (Typ.) | | | | | | |
| а | 18 | 1.8V (Typ.) | 30 | 3.0V (Typ.) | | | | | | |
| | 25 | 2.5V (Typ.) | 31 | 3.1V (Typ.) | | | | | | |
| | 28 | 2.8V (Typ.) | 33 | 3.3V (Typ.) | | | | | | |
| b | Package: | HFV : HVSC | DF6 | | | | | | | |
| | | | | | | | | | | |

b

S

Absolute maximum ratings (Ta = 25°C)

| Parameter | Symbol | Limits | Unit | |
|---|----------------|--|-------------|--|
| Applied supply voltage | VMAX | -0.3 ~ +6.5 | V | |
| | | 680 *1(HVSOF6) | | |
| Power dissipation | Pd | 410 *2(HVSOF5) | mW | |
| | | 540 *3(SSOP5) | | |
| Operating temperature range | Topr | -40 ^{*4} ~ +85 | °C | |
| Storage temperature range | Tstg | -55 ~ +125 | °C | |
| * 1 Derated at 6.8mW/°C for temperature | above Ta = 25° | C. when mounted on a glass epoxy PCB (70 | mm X 1.6 mm | |

* 1 Derated at 0-5mmVr⊂ for temperature above 1a = 25°C, when mounted on a glass epoxy PCB (70 mm X1.6 mm).
* 2 Derated at 4.1mW/r⊂ for temperature above Ta = 25°C, when mounted on a glass epoxy PCB (70 mm X1.6 mm).
* 3 Derated at 5-4mW/r⊂ for temperature above Ta = 25°C, when mounted on a glass epoxy PCB (70 mm X1.6 mm).
* 4 BH□□FB1W series: -30°C and up.

Recommended operating range

| Parameter | | Symbol | Min. | Тур. | Max. | Unit |
|-------------------|--------|--------|------|------|------|------|
| Power supply volt | age | VIN | 2.5 | - | 5.5 | V |
| | BHMA3W | | _ | - | 300 | mA |
| Output current | BHFB1W | IOUT | - | - | 150 | mA |
| | BHLB1W | | - | - | 150 | mA |

Recommended operating conditions

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|--------------------------|--------|-------------------|------|------|------|-------------------------------|
| Input capacitor | CIN | 0.1 *1 | - | - | μF | Ceramic capacitor recommended |
| Output capacitor | Co | 1.0 ^{*2} | - | - | μF | Ceramic capacitor recommended |
| Noise decrease capacitor | Cn | - | 0.01 | 0.22 | μF | Ceramic capacitor recommended |

* 2 The output may become unstable at low temperatures and with light loads, so a capacitance of 2.2 µF or much more is recommended when using at low temperatures. (BH = FB1W)

● Electrical characteristics (Unless otherwise noted, Ta=25°C, VIN=VoUT+1V^{*2}, STBY=1.5V, CIN=0.1μF, Co=1μF) BH FB1WHFV/WG, BH LB1WHFV/WG

| | 11F V/VVG | $, $ D \Box | | 100 | | | |
|-------------------------|-----------------|--|-------------|------|-------------|------|---------------------------------|
| Paramet | er | Symbol | Min. | Тур. | Max. | Unit | Conditions |
| Output voltage*1 | | Vout | Vout x 0.99 | Vout | Vouт x 1.01 | V | Ιουτ=1mA |
| Circuit current | | I GND | - | 40 | 70 | μA | lout=50mA |
| Circuit current (S | TBY) | I STBY | - | - | 1.0 | μA | STBY=0V |
| Ripple rejection r | atio | RR | - | 70 | - | dB | VRR=-20dBv, fRR=1kHz, Iout=10mA |
| Load response 1 | | LTV1 | - | 50 | - | mV | louт=1mA to 30mA |
| Load response 2 | | LTV2 | - | 50 | - | mV | louт=30mA to 1mA |
| Dropout voltage* | 3 | VSAT | - | 250 | 450 | mV | VIN=0.98 X VOUT, IOUT=100mA |
| Line regulation | | VDL1 | - | 2 | 20 | mV | VIN=VOUT+0.5V to 5.5V *4 |
| Load regulation | | VDL01 | - | 10 | 30 | mV | IOUT=1mA to 100mA |
| Over current protection | limit current*3 | ILMAX | - | 250 | - | mA | Vo=Vout X 0.98 |
| Short current*3 | | I SHORT | - | 50 | - | mA | Vo=0V |
| STBY pull-down | resistor | RSTB | 550 | 1100 | 2200 | k | |
| STBY | ON | VSTBH | 1.5 | _ | Vin | V | |
| control voltage | OFF | VSTBL | -0.3 | _ | 0.3 | V | |
| | | | | | | | |

* This product is not designed for protection against radio active rays.
 *1 BH15, 18LB1WHFV/WG: ±25 mV precision
 *2 BH15, 18LB1WHFV/WG: VIN = 3.5 V

*3 Excluding BH15, 18LB1WHFV/WG *4 BH15, 18LB1WHFV/WG: VIN = 3.0 to 5.5 V

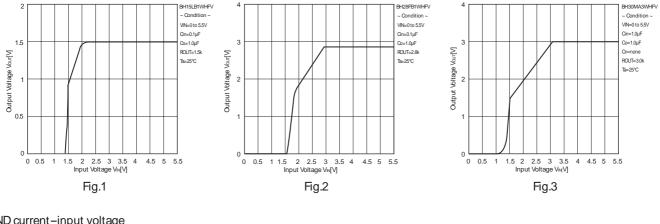
● Electrical characteristics (Unless otherwise noted, Ta=25°C, VIN=VouT+1V*4, STBY=1.5V, CIN=1µF, Co=1µF) BH MA3WHFV

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---------------------------------------|----------|-------------|------|-------------|--------|---------------------------------|
| Output voltage*1 | Vout | Vout x 0.99 | Vout | Vout x 1.01 | V | IOUT=1mA |
| Circuit current | I GND | - | 65 | 95 | μA | Ιουτ=1mA |
| Circuit current (STBY) | I STBY | - | - | 1.0 | μA | STBY=0V |
| Ripple rejection ratio | RR | - | 60 | - | dB | VRR=-20dBv, fRR=1kHz, Iout=10mA |
| Dropout voltage*2 | VSAT1 | - | 60 | 90 | mV | VIN=0.98 X VOUT, IOUT=100mA |
| Line regulation | VDL1 | - | 2 | 20 | mV | VIN=VOUT+0.5V to 5.5V *3 |
| Load regulation 1 | VDL01 | - | 6 | 30 | mV | IOUT=1mA to 100mA |
| Load regulation 2 | VDL02 | - | 18 | 90 | mV | IOUT=1mA to 300mA |
| Output voltage temperature | ΔVουτ/ΔΤ | _ | ±100 | - | ppm/°C | Іоυт=1mA, Ta=-40 to +85°С |
| Over current protection limit current | ILMAX | - | 600 | - | mA | Vo=Vout X 0.85 |
| Short current | I SHORT | - | 100 | - | mA | Vo=0V |

* This product is not designed for protection against radio active rays. *1 BH15, 18MA3WHFV: ±25 mV precision *3 BH15, 18MA3WHFV: 3.0 to 5.5 V *2 Excluding BH15, 18MA3WHFV *4 BH15, 18MA3WHFV: 3.5 V

• Typical characteristics

Output voltage-input voltage



BH28FB1WHEV

- Condition -

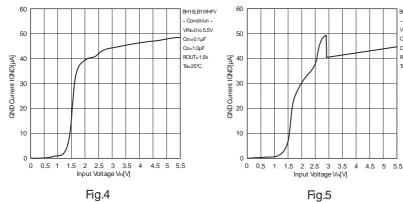
VIN=0 to 5.5V

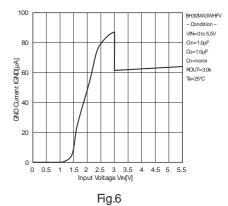
Cin=0.1µF

Co=1.0µF

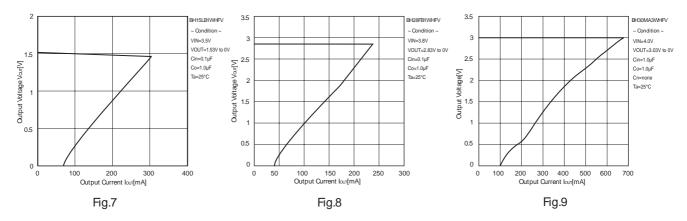
ROUT=2.8k Ta=25°C

• GND current-input voltage

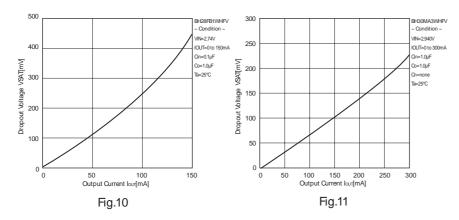




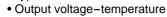
• Output voltage-output current

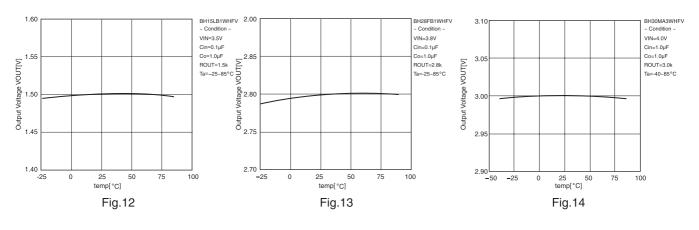




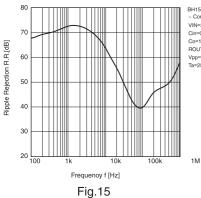


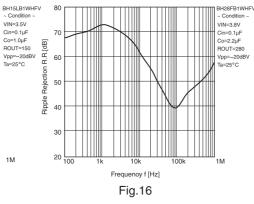
Typical Characteristics

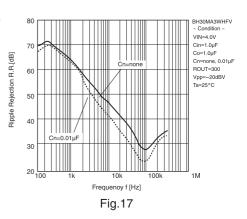




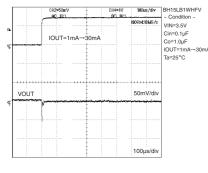
• Ripple reflection-frequency



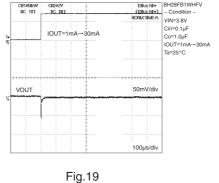




• Load response characteristics (CO = 1.0 μ F)







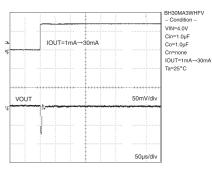
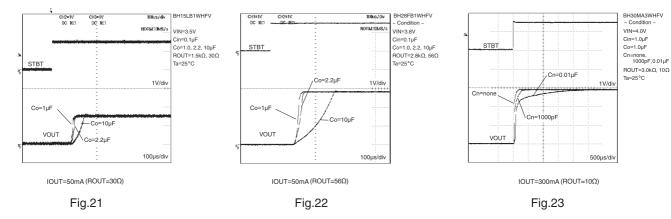
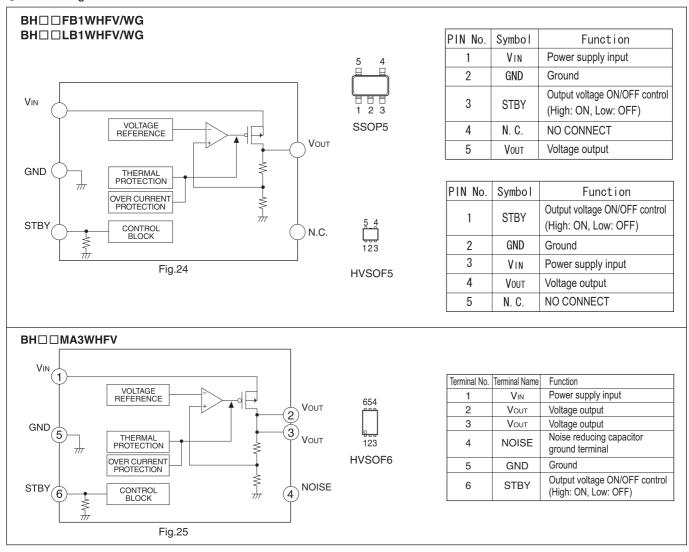


Fig.20

• Output voltage startup time



Block diagrams

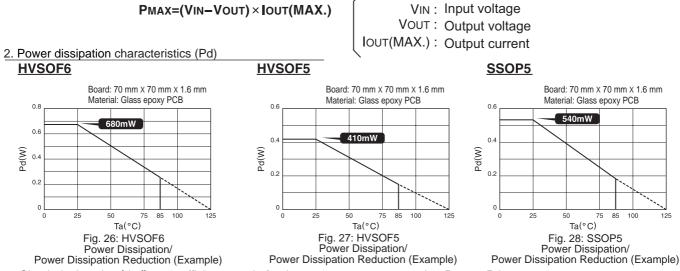


• Power dissipation Pd

1. Power dissipation

Power dissipation calculation include estimates of power dissipation characteristics and internal IC power consumption and should be treated as guidelines. In the event that the IC is used in an environment where this power dissipation is exceeded, the attendant rise in the junction temperature will trigger the thermal shutdown circuit, reducing the current capacity and otherwise degrading the IC's design performance. Allow for sufficient margins so that this power dissipation is not exceeded during IC operation.

Calculating the maximum internal IC power consumption (PMAX)

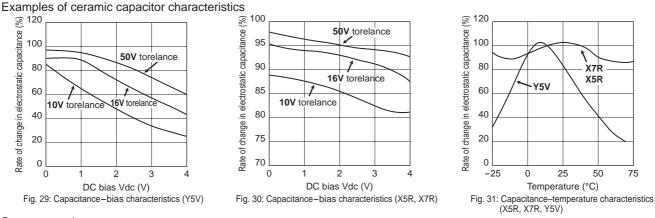


* Circuit design should allow a sufficient margin for the temperature range so that PMAX < Pd.

Input capacitor

It is recommended to insert bypass capacitors between input and GND pins, positioning them as close to the pins as possible. These capacitors will be used when the power supply impedance increases or when long wiring routes are used, so they should be checked once the IC has been mounted.

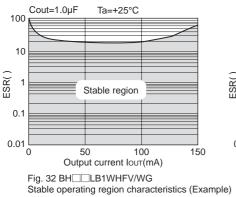
Ceramic capacitors generally have temperature and DC bias characteristics. When selecting ceramic capacitors, use X5R or X7R or better models that offer good temperature and DC bias characteristics and high torelant voltages.



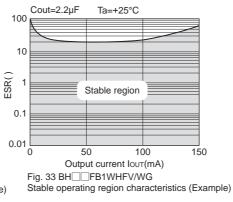
Output capacitor

To prevent oscillation at the output, it is recommended that the IC be operated at the stable region show in below Fig. It operates at the capacitance of more than 1.0μ F. As capacitance is larger, stability becomes more stable and characteristic of output load fluctuation is also improved.

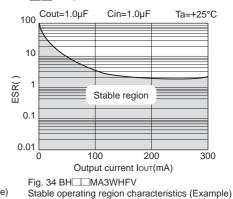
BH LB1WHFV/WG



BH FB1WHFV/WG



BH MA3WHFV



Other precautions

• Over current protection circuit

The IC incorporates a built-in over current protection circuit that operates according to the output current capacity. This circuit serves to protect the IC from damage when the load is shorted. The protection circuits use fold-back type current limiting and are designed to limit current flow by not latching up in the event of a large and instantaneous current flow originating from a large capacitor or other component. These protection circuits are effective in preventing damage due to sudden and unexpected accidents. However, the IC should not be used in applications characterized by the continuous operation or transitioning of the protection circuits.

• Thermal shutdown circuit

This system has a built-in thermal shutdown circuit for the purpose of protecting the IC from thermal damage. As shown above, this must be used within the range of power dissipation, but if the power dissipation happens to be continuously exceeded, the chip temperature increases, causing the thermal shutdown circuit to operate. When the thermal shutdown circuit operates, the operation of the circuit is suspended. The circuit resumes operation immediately after the chip temperature decreases, so the output repeats the ON and OFF states. There are cases in which the IC is destroyed due to thermal runaway when it is left in the overloaded state. Be sure to avoid leaving the IC in the overloaded state.

• Actions in strong magnetic fields

Use caution when using the IC in the presence of a strong magnetic field as such environments may occasionally cause the chip to malfunction.

Back current

In applications where the IC may be exposed to back current flow, it is recommended to create a route t dissipate this current by inserting a bypass diode between the VIN and VOUT pins.

GND potential

Ensure a minimum GND pin potential in all operating conditions.

In addition, ensure that no pins other than the GND pin carry a voltage less than or equal to the GND pin, including during actual transient phenomena.

Noise terminal (BH MA3WHFV)

The terminal is directly connected to inward normal voltage source. Because this has low current ability, load exceeding 100nA will cause some instability at the output. For such reasons, we urge you to use ceramic capacitors which have less leak current. When choosing noise the current reduction capacitor, there is a trade-off between boot-up time and stability. A bigger capacitor value will result in lesser oscillation but longer boot-up time for VOUT.

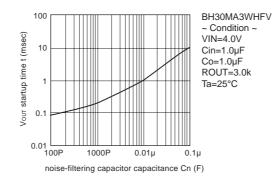


Fig. 35: Vout startup time vs. noise-filtering capacitor capacitance characteristics (Example)

Regarding input pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P/N junctions are formed at the intersection of these P layers with the N layers of other elements to create a variety of parasitic elements. For example, when a resistor and transistor are connected to pins as shown in Fig.37

- \bigcirc The P/N junction functions as a parasitic diode when GND > (Pin A) for the resistor or GND > (Pin B) for the transistor (NPN).
- Similarly, when GND > (Pin B) for the transistor (NPN), the parasitic diode described above combines with the N layer of other adjacent elements to operate as a parasitic NPN transistor.

The formation of parasitic elements as a result of the relationships of the potentials of different pins is an inevitable result of the IC's architecture. The operation of parasitic elements can cause interference with circuit operation as well as IC malfunction and damage. For these reasons, it is necessary to use caution so that the IC is not used in a way that will trigger the operation of parasitic elements, such as by the application of voltage lower than the GND (P substrate) voltage to input pins.

FB1:150mA

LB1 : 150mA

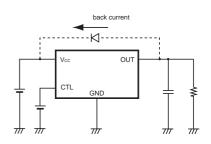
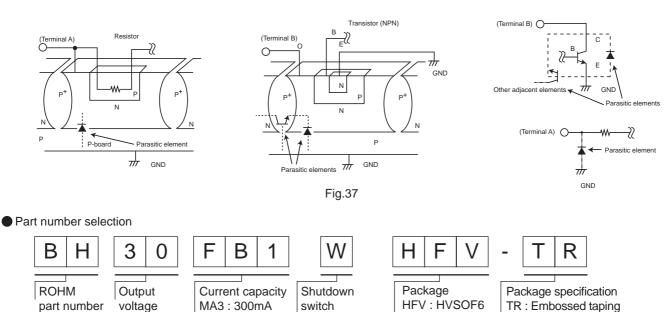


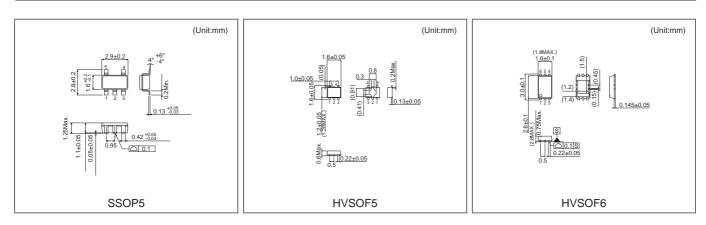
Fig. 36: Example of bypass diode connection

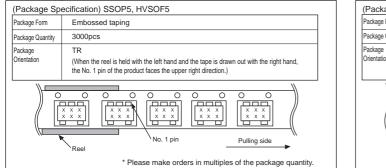


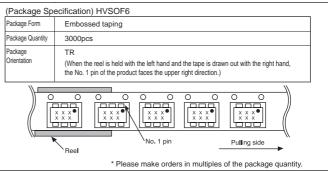
HVSOF5

G:SSOP5

W: With switch







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